

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.6			V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	- 0.6			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	N-Ch P-Ch			± 100 ± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			- 1	
		$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$	N-Ch			5	
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$	P-Ch			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	N-Ch	1			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	- 1			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 0.66\text{ A}$	N-Ch		0.320	0.385	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -0.41\text{ A}$	P-Ch		0.850	0.995	
		$V_{GS} = 2.5\text{ V}, I_D = 0.40\text{ A}$	N-Ch		0.560	0.630	
		$V_{GS} = -2.5\text{ V}, I_D = -0.25\text{ A}$	P-Ch		1.400	1.800	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 0.66\text{ A}$	N-Ch		1.5		S
		$V_{DS} = -10\text{ V}, I_D = -0.41\text{ A}$	P-Ch		0.8		
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.23\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.8	1.2	V
		$I_S = -0.23\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		- 0.8	- 1.2	
Dynamic ^b							
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.66\text{ A}$	N-Ch		0.8	1.2	nC
Gate-Source Charge	Q_{gs}		P-Ch		1.2	1.8	
Gate-Drain Charge	Q_{gd}	P-Channel $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -0.41\text{ A}$	N-Ch		0.06		
			P-Ch		0.45		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 20\text{ }\Omega$ $I_D \equiv 0.5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		10	20	ns
			P-Ch		7.5	15	
Rise Time	t_r		N-Ch		16	30	
			P-Ch		20	40	
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -10\text{ V}, R_L = 20\text{ }\Omega$ $I_D \equiv -0.5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		10	20	
			P-Ch		8.5	17	
Fall Time	t_f		N-Ch		10	20	
			P-Ch		12	24	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 0.23\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		20	40	
		$I_F = -0.23\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	P-Ch		25	40	

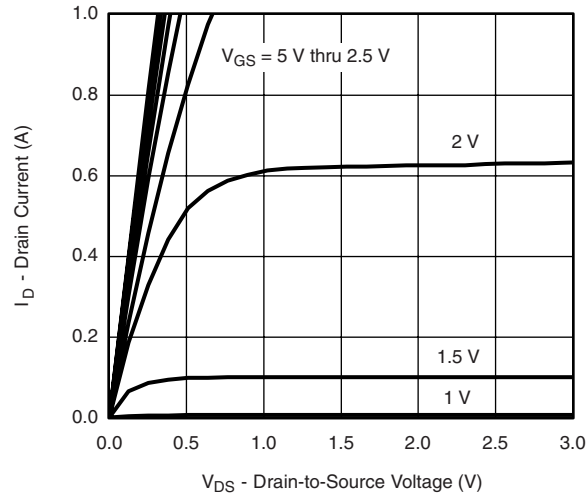
Notes:

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

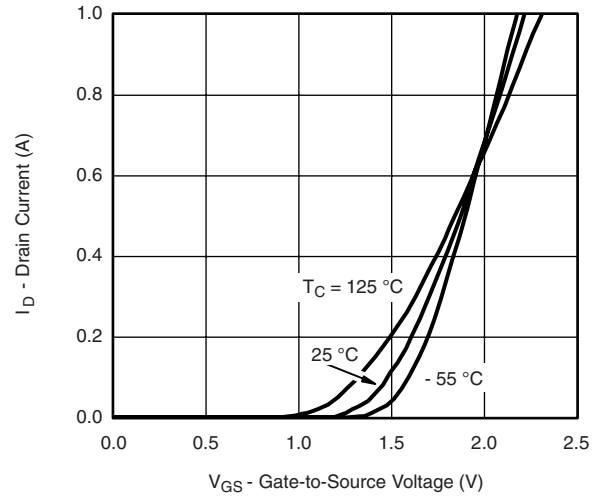
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

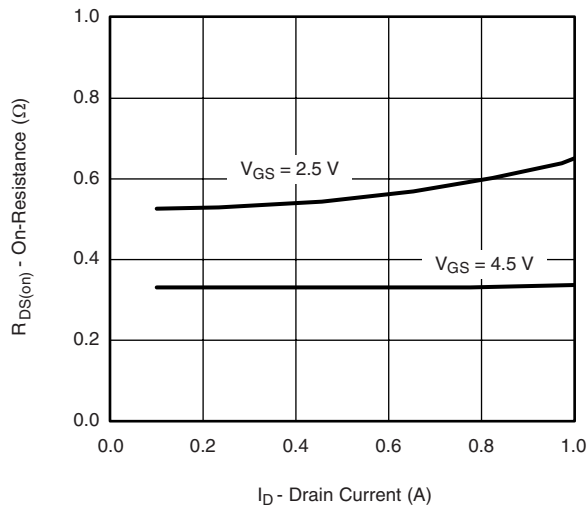
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



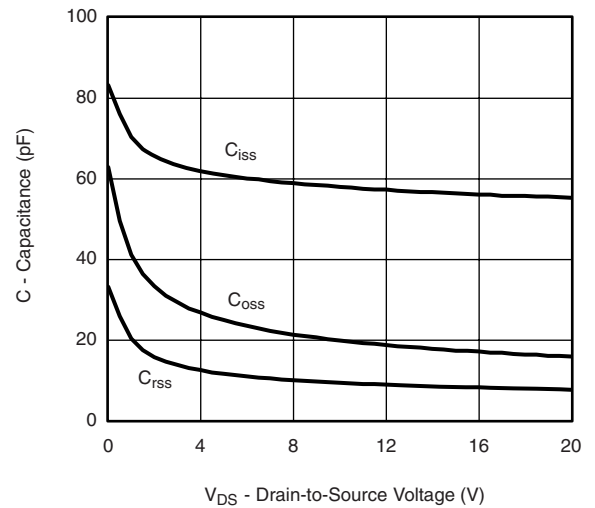
Output Characteristics



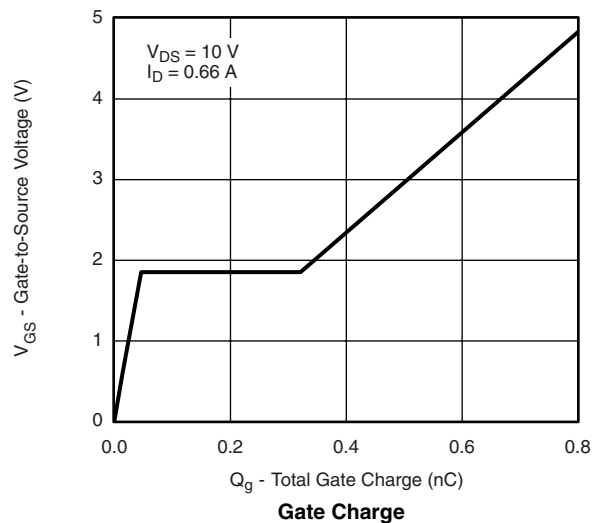
Transfer Characteristics



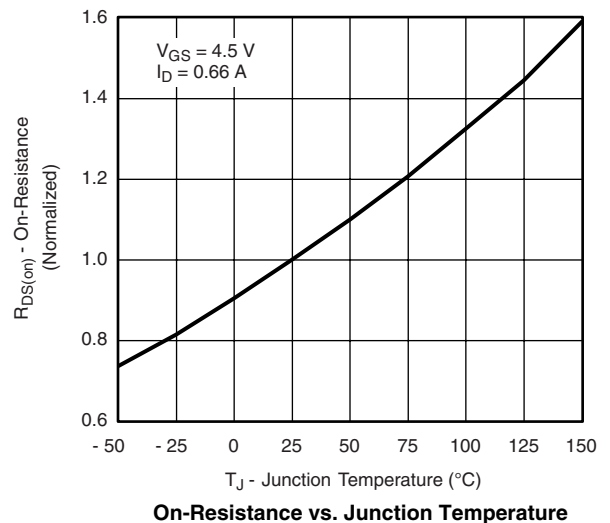
On-Resistance vs. Drain Current



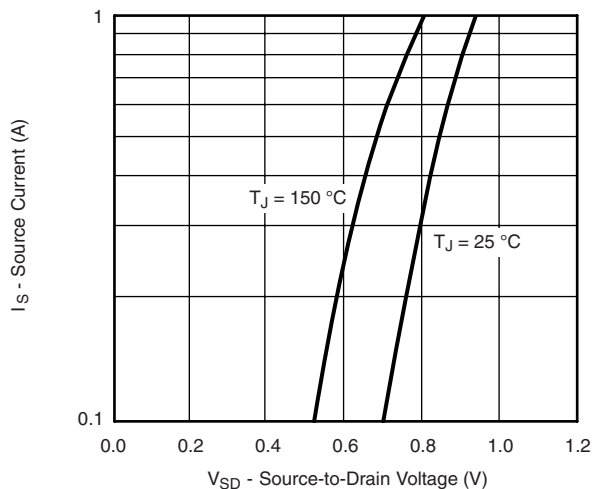
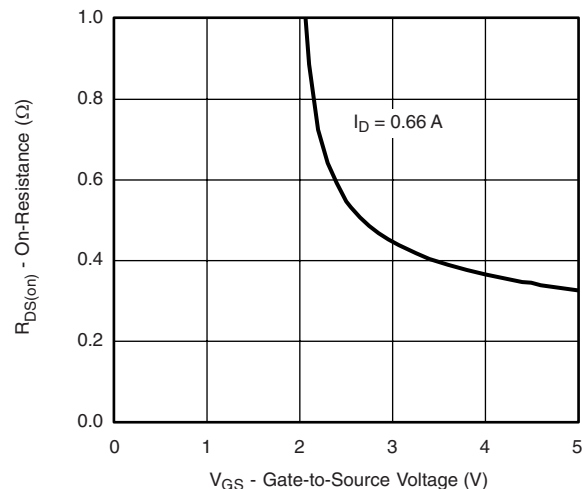
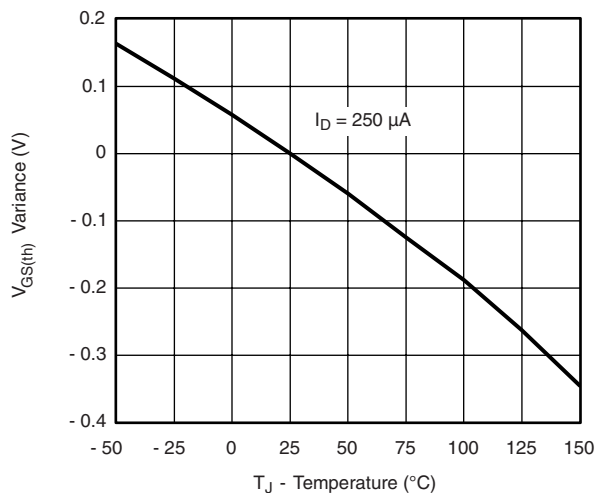
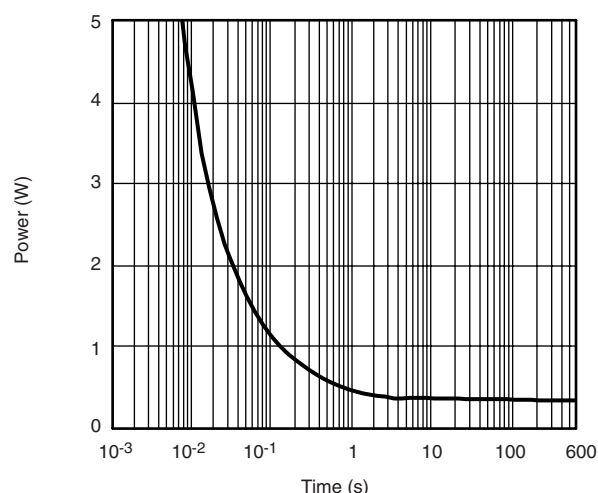
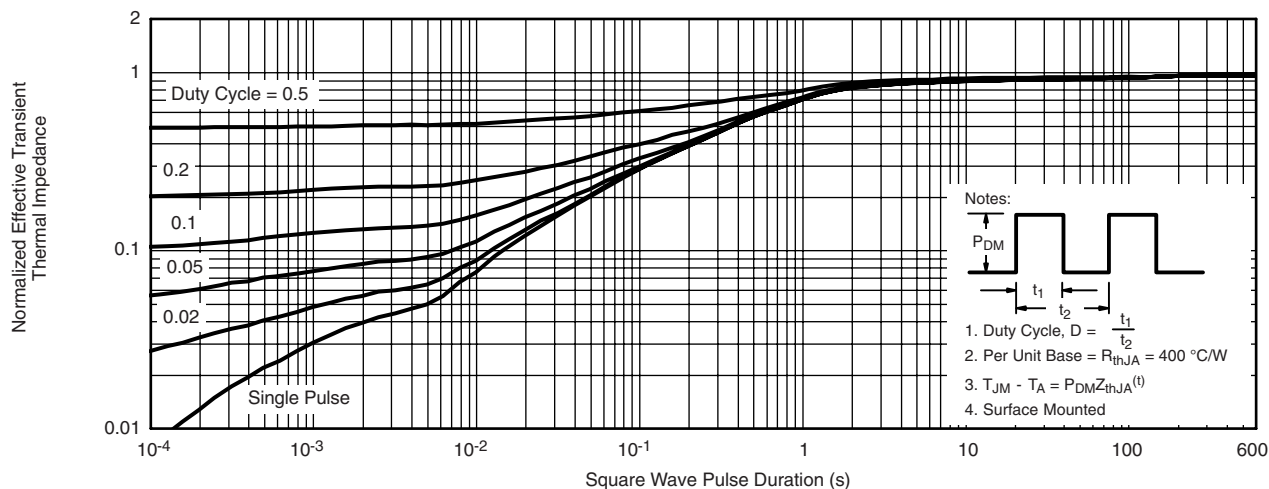
Capacitance



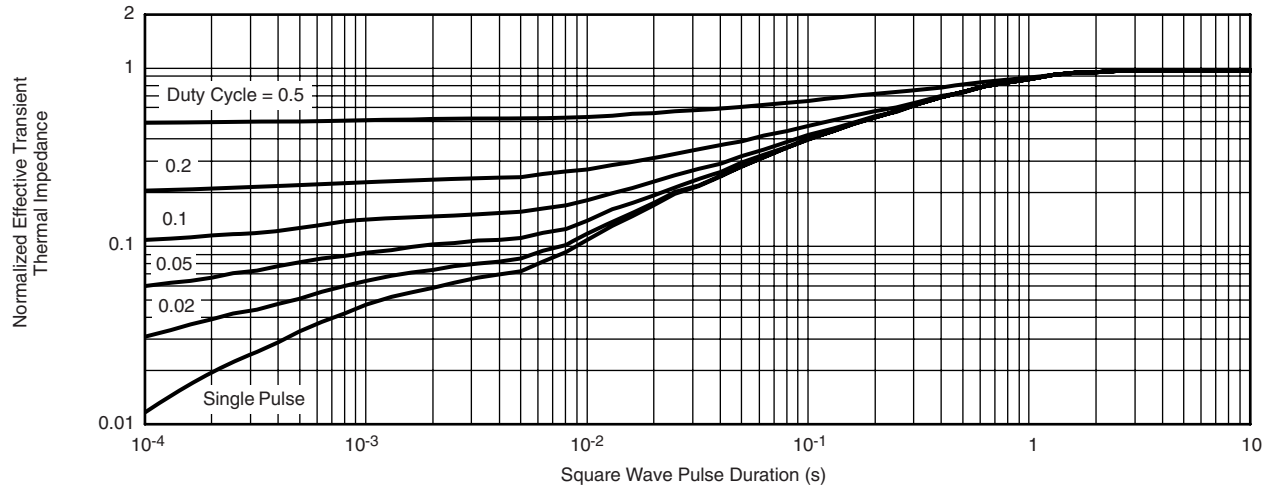
Gate Charge



On-Resistance vs. Junction Temperature

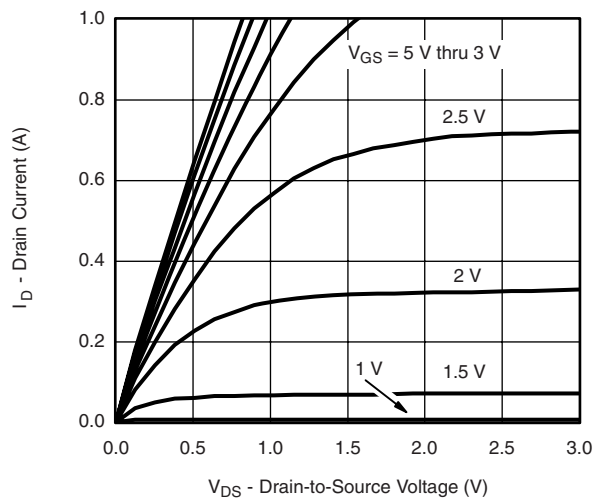
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Normalized Thermal Transient Impedance, Junction-to-Ambient**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

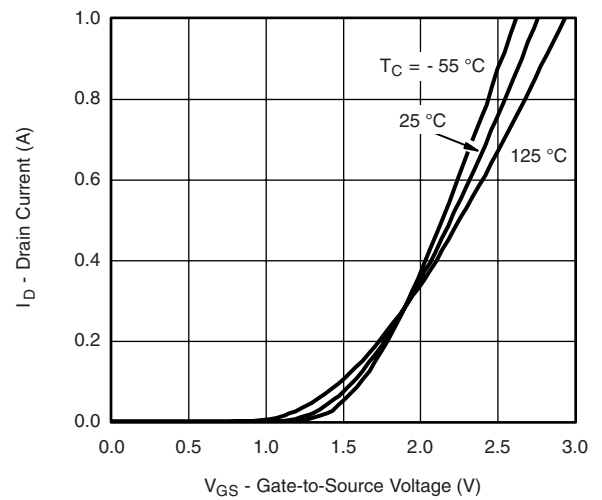


Normalized Thermal Transient Impedance, Junction-to-Foot

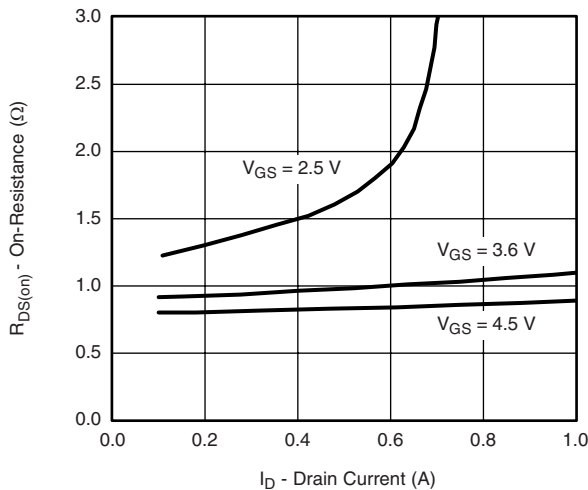
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



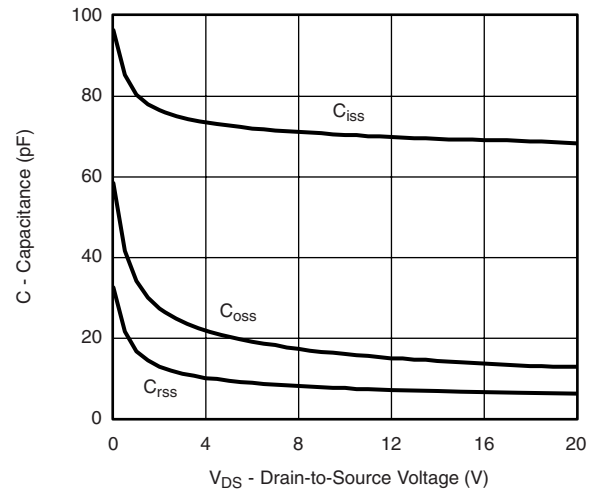
Output Characteristics



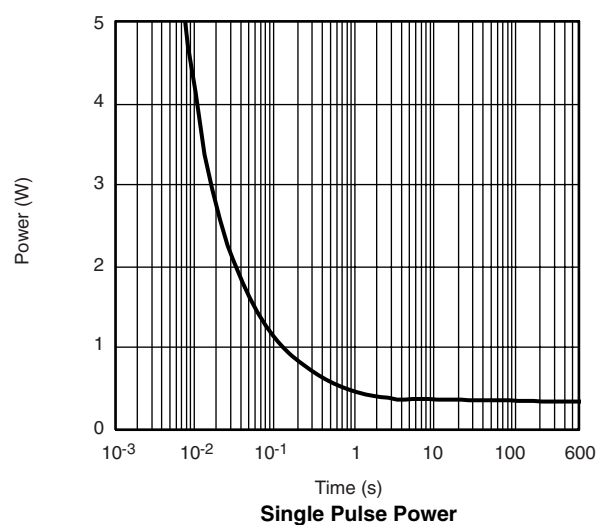
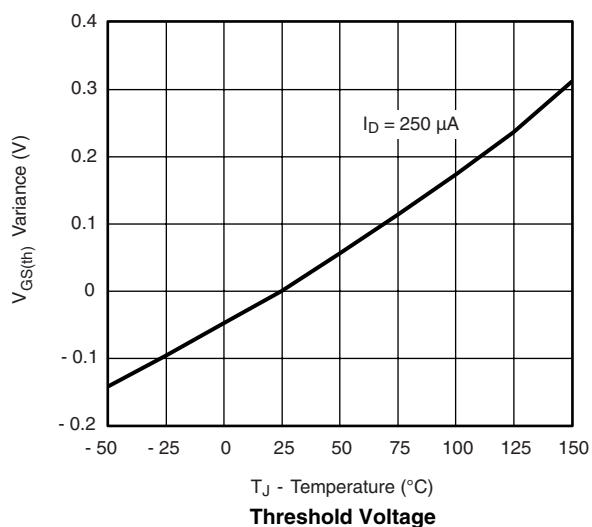
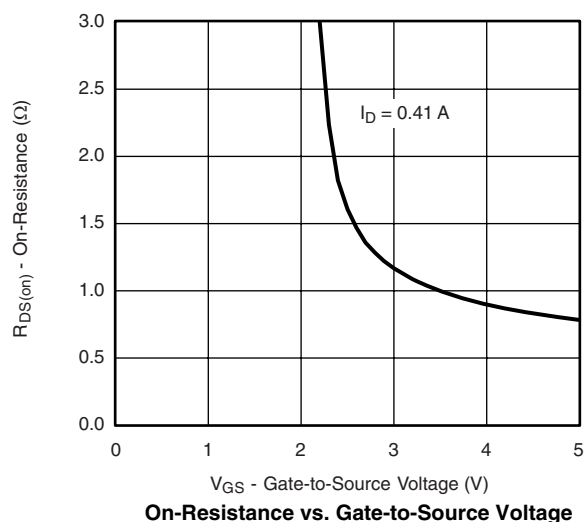
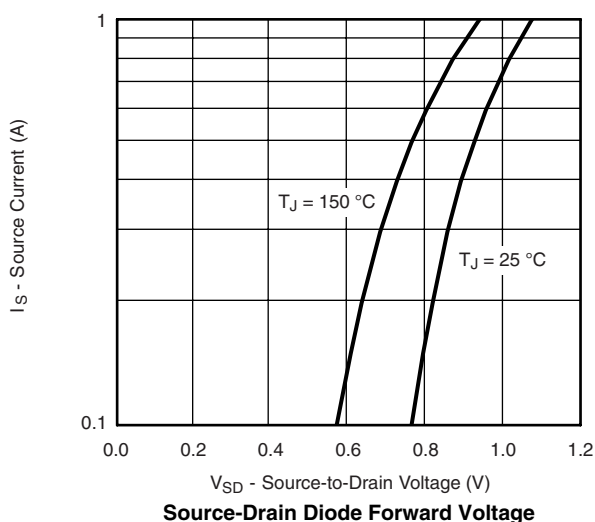
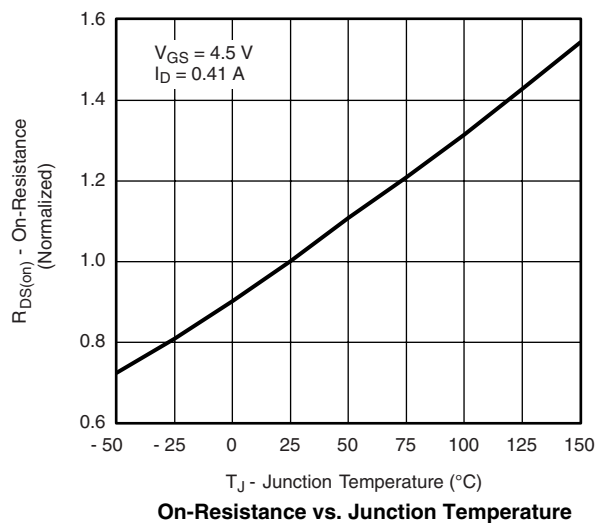
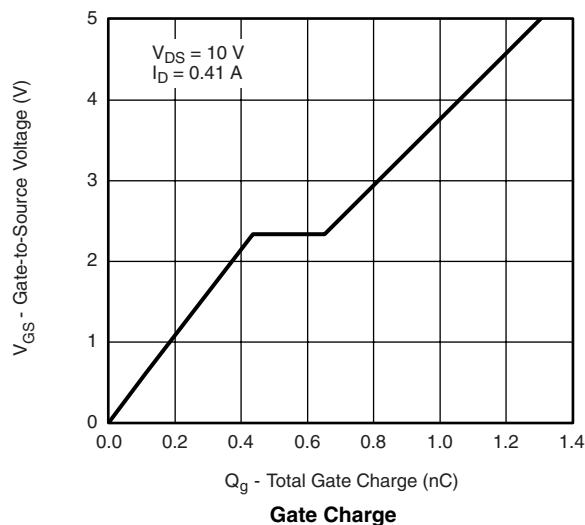
Transfer Characteristics



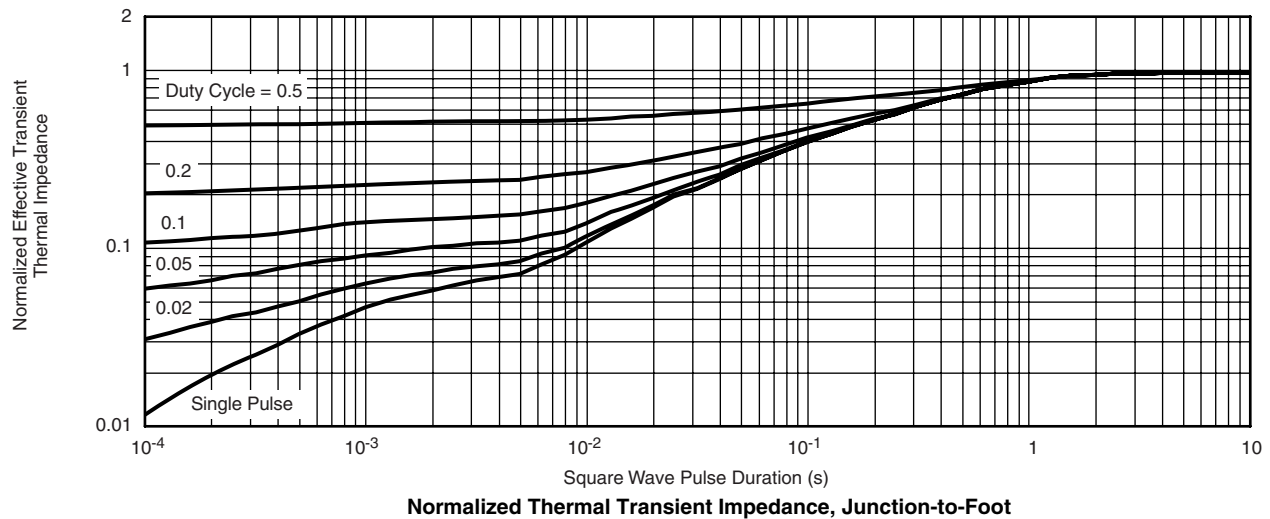
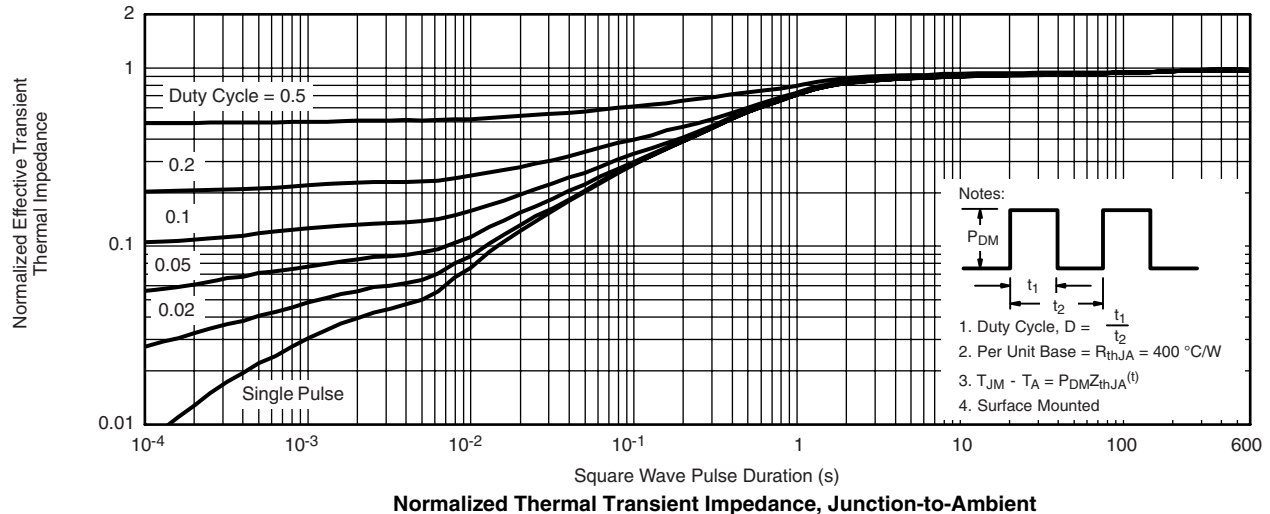
On-Resistance vs. Drain Current



Capacitance

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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